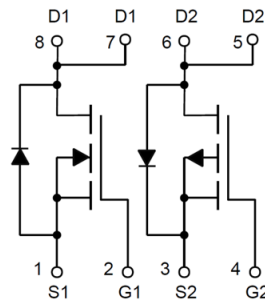
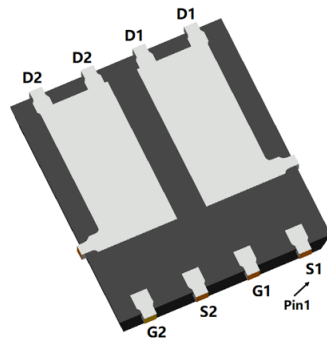
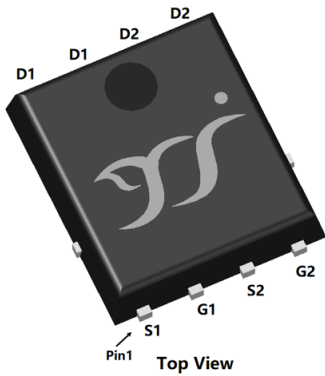


## N-Channel and P-Channel Complementary MOSFET



PDFN5060-8L

### Product Summary

- NMOS**
- $V_{DS}$  100V
  - $I_D$  40A
  - $R_{DS(ON)}$  (at  $V_{GS}=10V$ )  $< 19m\Omega$
  - $R_{DS(ON)}$  (at  $V_{GS}=4.5V$ )  $< 23m\Omega$

- PMOS**
- $V_{DS}$  -100V
  - $I_D$  -12A
  - $R_{DS(ON)}$  (at  $V_{GS}=-10V$ )  $< 109m\Omega$
  - $R_{DS(ON)}$  (at  $V_{GS}=-4.5V$ )  $< 120m\Omega$

- 100% EAS Tested

### General Description

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

### Applications

- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

### ■ Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	NMOS	PMOS	Unit
Drain-source Voltage		$V_{DS}$	100	-100	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	$\pm 20$	V
Drain Current	$T_A=25^\circ C$	$I_D$	6.8	-2.8	A
	$T_A=100^\circ C$		4.3	-1.8	
	$T_C=25^\circ C$		40	-12	
	$T_C=100^\circ C$		25	-7.6	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	120	-40	A
Avalanche energy <sup>B</sup>		EAS	72	64	mJ
Total Power Dissipation <sup>C</sup>	$T_A=25^\circ C$	$P_D$	2	2	W
	$T_A=100^\circ C$		0.8	0.8	
	$T_C=25^\circ C$		69	44	
	$T_C=100^\circ C$		27	17	
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~+150	-55~+150	$^\circ C$

### ■ Thermal resistance

Parameter		Symbol	NMOS		PMOS		Units
			Typ	Max	Typ	Max	
Thermal Resistance Junction-to-Ambient <sup>D</sup>	Steady-State	$R_{\theta JA}$	50	60	50	60	$^\circ C/W$
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	1.5	1.8	2.3	2.8	

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG12NP10B	F1	YJG12NP10B	5000	10000	100000	13" reel



# YJG12NP10B

## ■ NMOS Electrical Characteristics ( $T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=100V, V_{GS}=0V$	-	-	1	$\mu A$
		$V_{DS}=100V, V_{GS}=0V, T_J=150^\circ\text{C}$	-	-	100	
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.8	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	15	19	m $\Omega$
		$V_{GS}=4.5V, I_D=5A$	-	18	23	
Diode Forward Voltage	$V_{SD}$	$I_S=20A, V_{GS}=0V$	-	-	1.2	V
Gate resistance	$R_G$	$f=1\text{MHz}$	-	1.5	-	$\Omega$
Maximum Body-Diode Continuous Current	$I_S$		-	-	40	A
<b>Dynamic Parameters</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=50V, V_{GS}=0V, f=1\text{MHz}$	-	1150	-	$\mu F$
Output Capacitance	$C_{oss}$		-	430	-	
Reverse Transfer Capacitance	$C_{rss}$		-	8	-	
<b>Switching Parameters</b>						
Total Gate Charge	$Q_g$	$V_{GS}=10V, V_{DS}=50V, I_D=20A$	-	20	-	nC
Gate-Source Charge	$Q_{gs}$		-	5.6	-	
Gate-Drain Charge	$Q_{gd}$		-	2.8	-	
Reverse Recovery Charge	$Q_{rr}$	$I_F=20A, di/dt=100A/\mu s$	-	32	-	nC
Reverse Recovery Time	$t_{rr}$		-	41	-	ns
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DD}=50V, I_D=20A$ $R_{GEN}=3\Omega$	-	7	-	ns
Turn-on Rise Time	$t_r$		-	29	-	
Turn-off Delay Time	$t_{D(off)}$		-	18	-	
Turn-off fall Time	$t_f$		-	7	-	



# YJG12NP10B

## ■ PMOS Electrical Characteristics ( $T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-100	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-100V, V_{GS}=0V$	-	-	-1	$\mu A$
		$V_{DS}=-100V, V_{GS}=0V, T_J=150^\circ\text{C}$	-	-	-100	
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.8	-2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-12A$	-	84	109	m $\Omega$
		$V_{GS}=-4.5V, I_D=-3A$	-	89	120	
Diode Forward Voltage	$V_{SD}$	$I_S=-12A, V_{GS}=0V$	-	-	-1.2	V
Gate resistance	$R_G$	$f=1\text{MHz}$	-	10	-	$\Omega$
Maximum Body-Diode Continuous Current	$I_S$		-	-	-12	A
<b>Dynamic Parameters</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=-50V, V_{GS}=0V, f=1\text{MHz}$	-	1060	-	pF
Output Capacitance	$C_{oss}$		-	110	-	
Reverse Transfer Capacitance	$C_{rss}$		-	8	-	
<b>Switching Parameters</b>						
Total Gate Charge	$Q_g$	$V_{GS}=-10V, V_{DS}=-50V, I_D=-10A$	-	19.5	-	nC
Gate-Source Charge	$Q_{gs}$		-	4.4	-	
Gate-Drain Charge	$Q_{gd}$		-	3.7	-	
Reverse Recovery Charge	$Q_{rr}$	$I_F=-10A, di/dt=100A/\mu s$	-	90	-	nC
Reverse Recovery Time	$t_{rr}$		-	59	-	ns
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=-10V, V_{DD}=-50V, I_D=-10A$ $R_{GEN}=3\Omega$	-	7.4	-	ns
Turn-on Rise Time	$t_r$		-	31	-	
Turn-off Delay Time	$t_{D(off)}$		-	48	-	
Turn-off fall Time	$t_f$		-	65	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. NMOS:  $T_J=25^\circ\text{C}$ ,  $V_G=10V$ ,  $R_G=25\Omega$ ,  $L=0.5\text{mH}$ ,  $I_{AS}=17A$ .

PMOS:  $T_J=25^\circ\text{C}$ ,  $V_G=-10V$ ,  $R_G=25\Omega$ ,  $L=0.5\text{mH}$ ,  $I_{AS}=-16A$ .

C.  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.

D. The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in the still air environment with  $T_A=25^\circ\text{C}$ .

The maximum allowed junction temperature of  $150^\circ\text{C}$ . The value in any given application depends on the user's specific board design.



# YJG12NP10B

## ■ NMOS Typical Electrical and Thermal Characteristics Diagrams

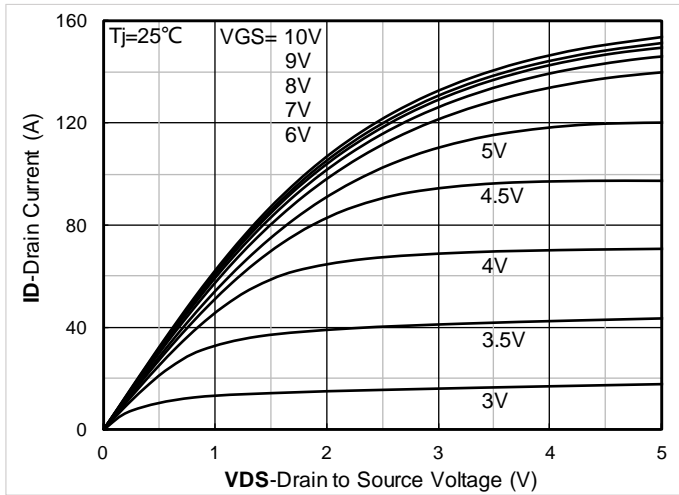


Figure 1. Output Characteristics

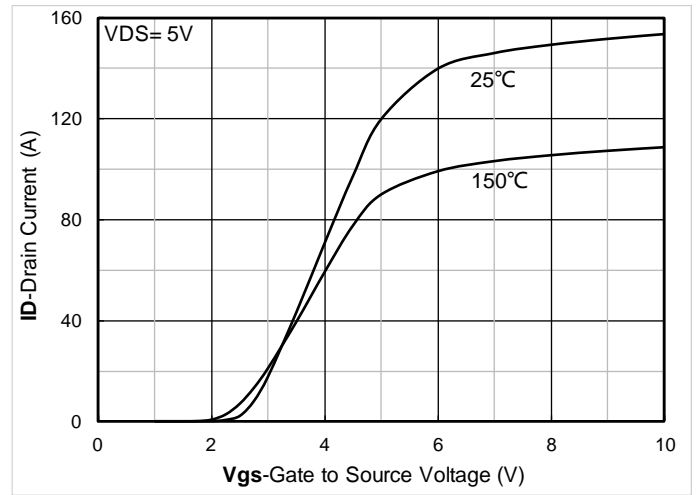


Figure 2. Transfer Characteristics

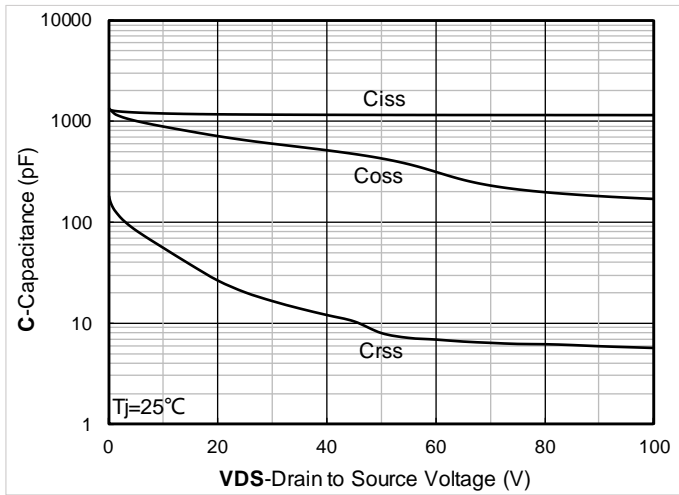


Figure 3. Capacitance Characteristics

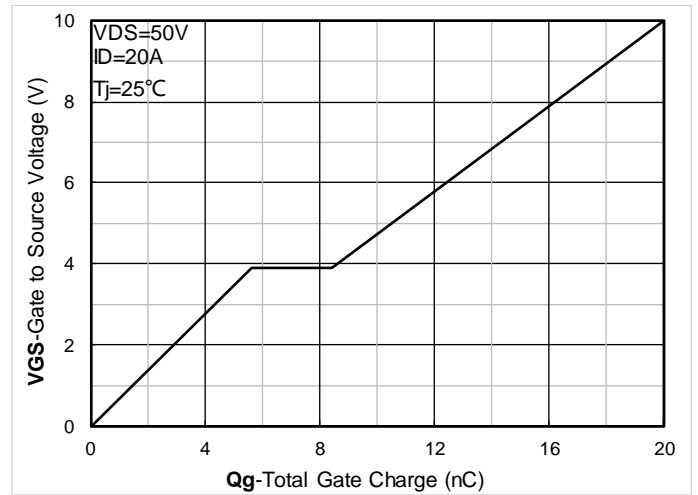


Figure 4. Gate Charge

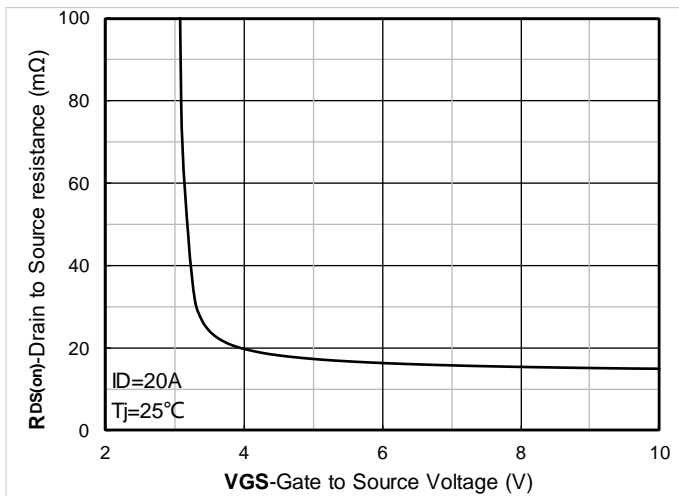


Figure 5. On-Resistance vs Gate to Source Voltage

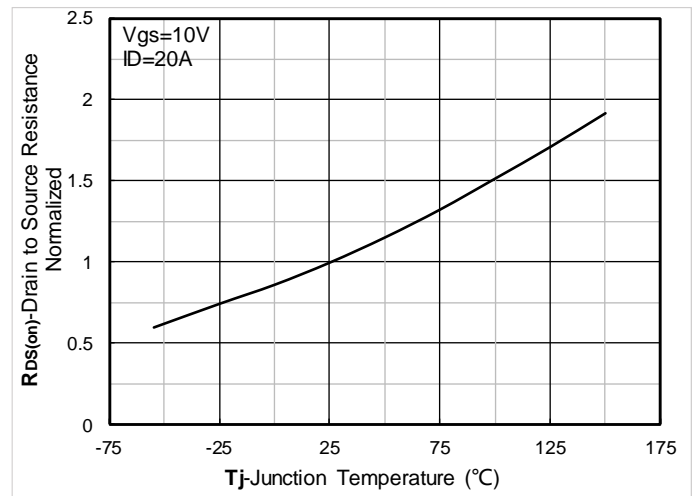


Figure 6. Normalized On-Resistance



# YJG12NP10B

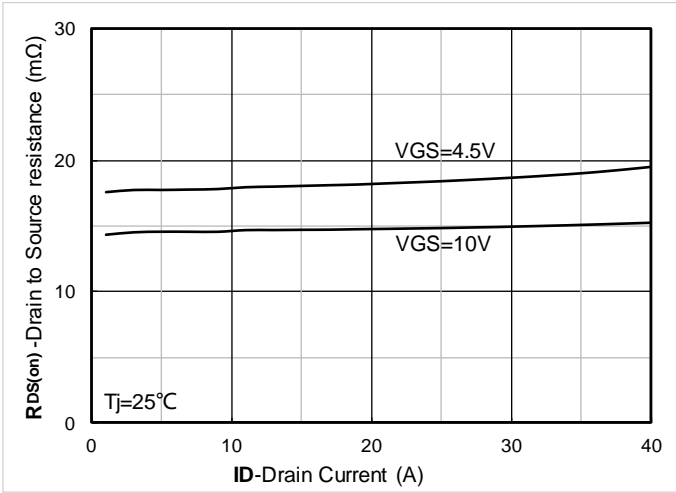


Figure 7.  $R_{DS(on)}$  VS Drain Current

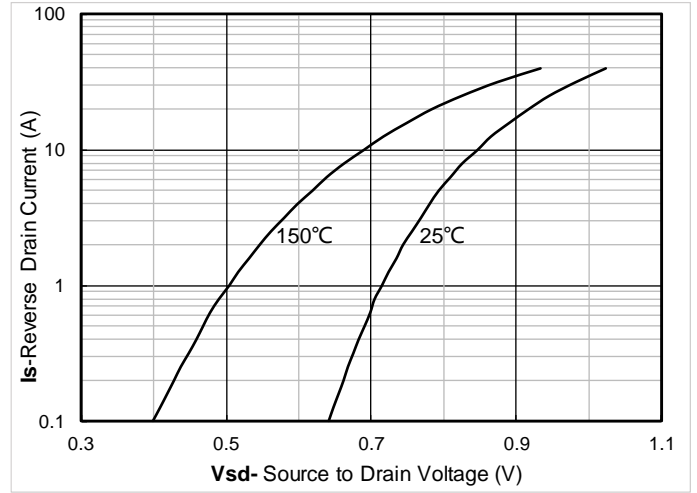


Figure 8. Forward characteristics of reverse diode

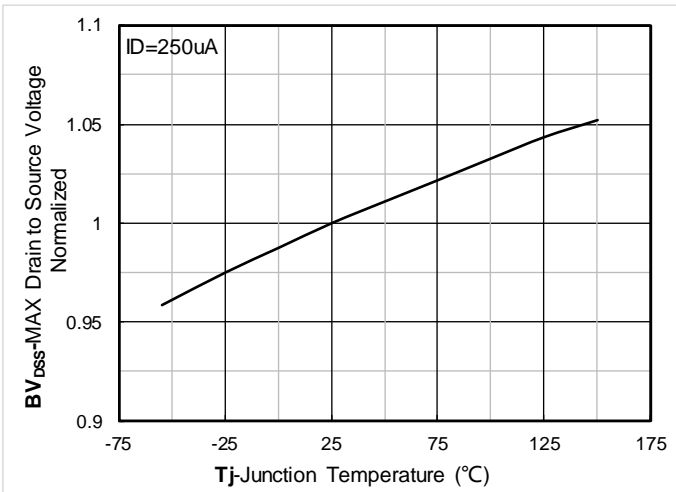


Figure 9. Normalized breakdown voltage

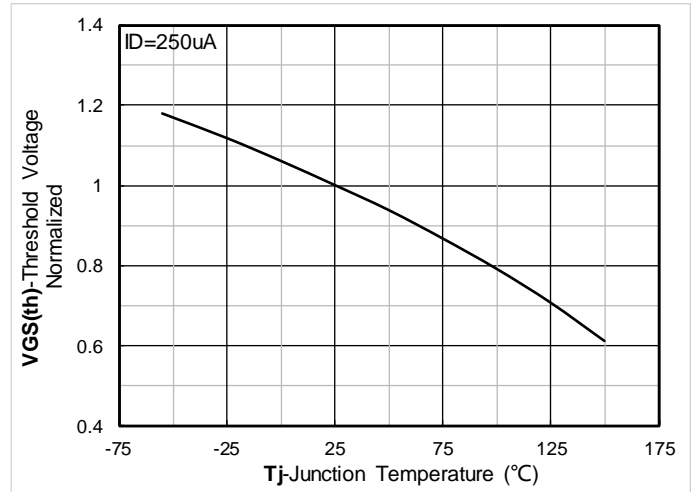


Figure 10. Normalized Threshold voltage

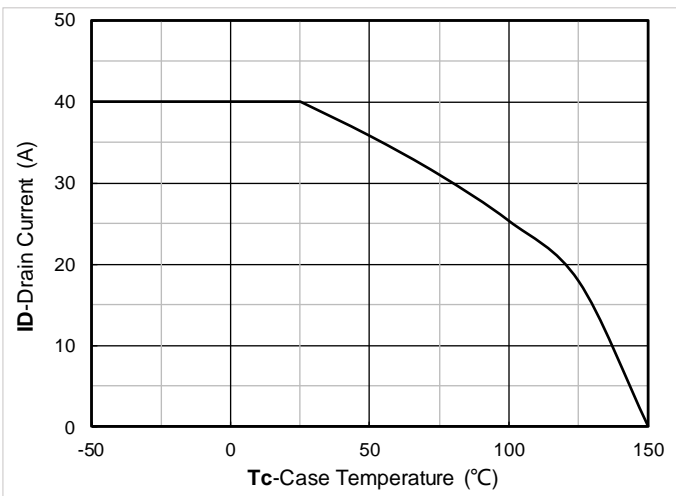


Figure 11. Current dissipation

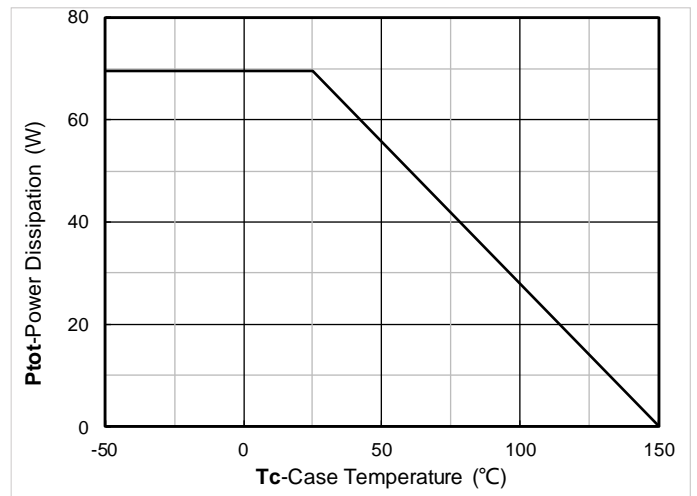


Figure 12. Power dissipation



# YJG12NP10B

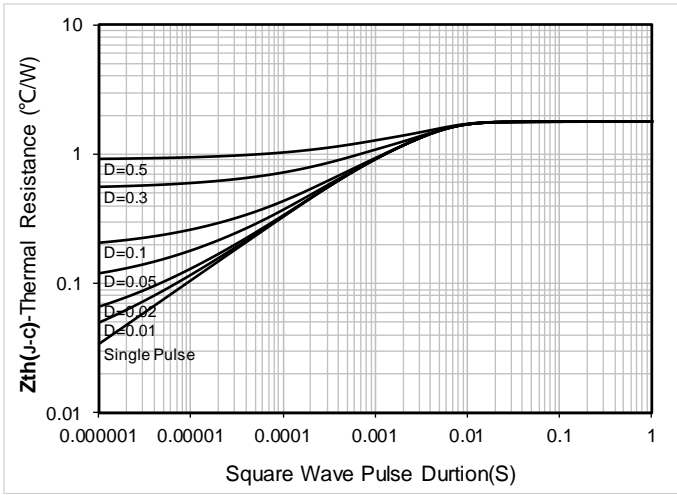


Figure 13. Maximum Transient Thermal Impedance

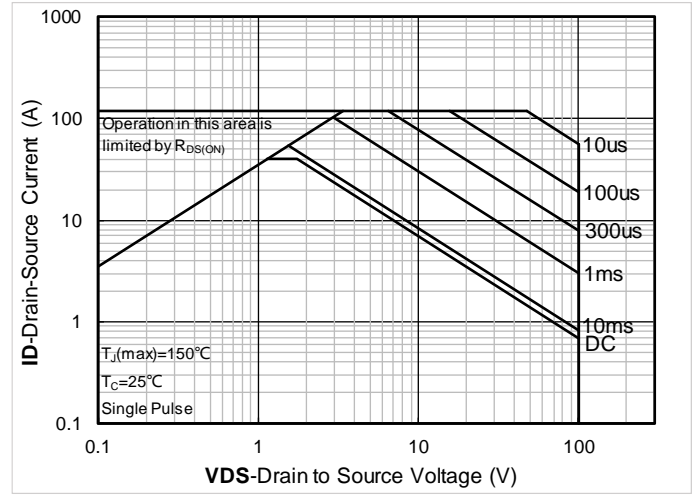


Figure 14. Safe Operation Area

## PMOS Typical Electrical and Thermal Characteristics Diagrams

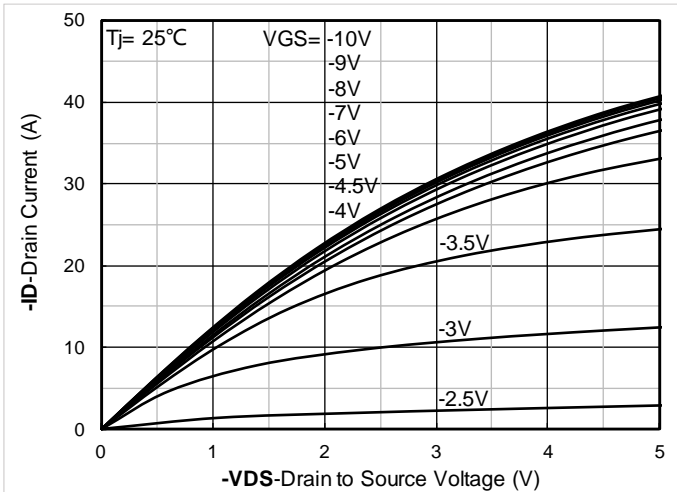


Figure 1. Output Characteristics

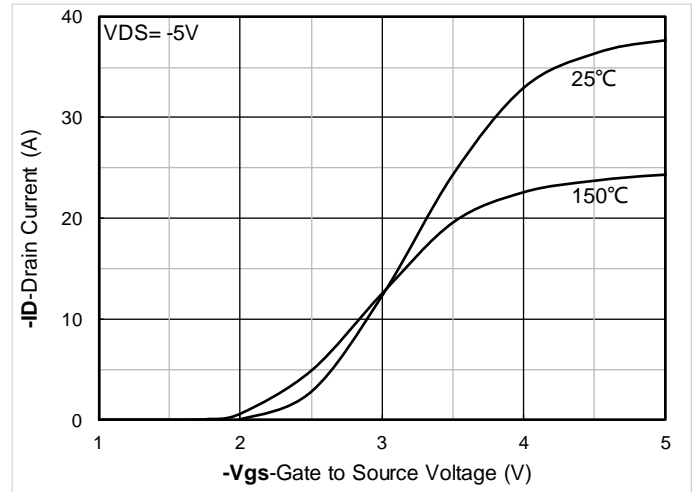


Figure 2. Transfer Characteristics

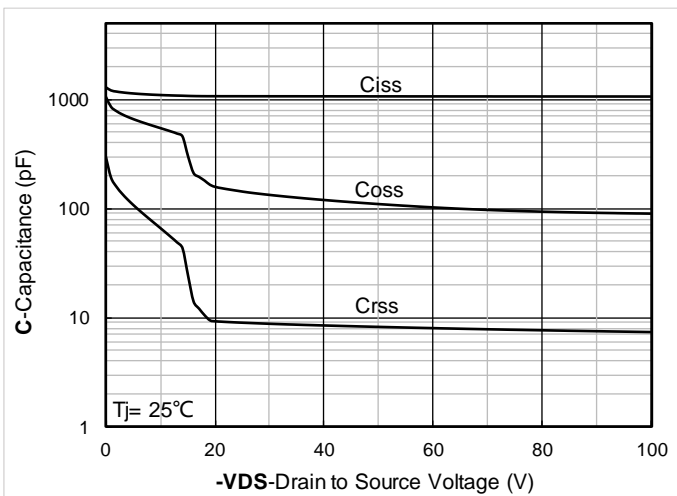


Figure 3. Capacitance Characteristics

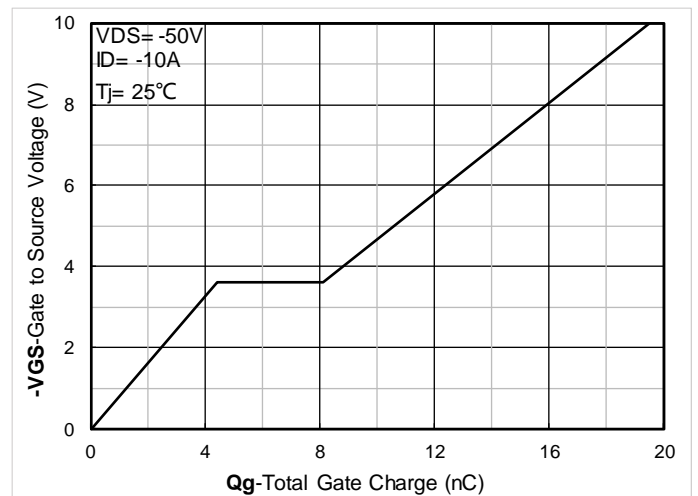


Figure 4. Gate Charge



# YJG12NP10B

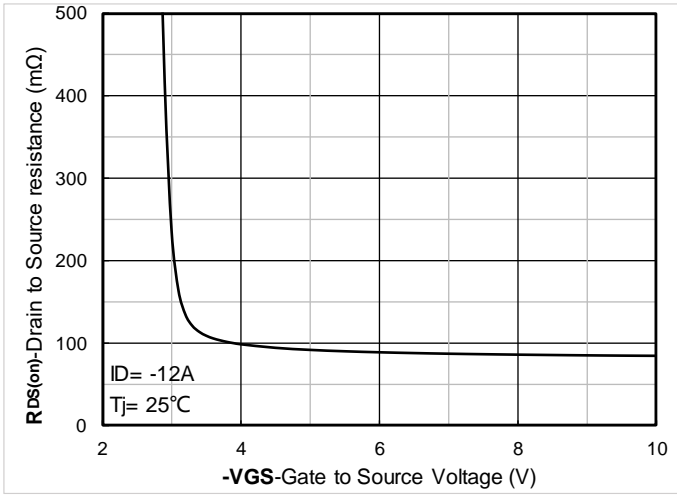


Figure 5. On-Resistance vs Gate to Source Voltage

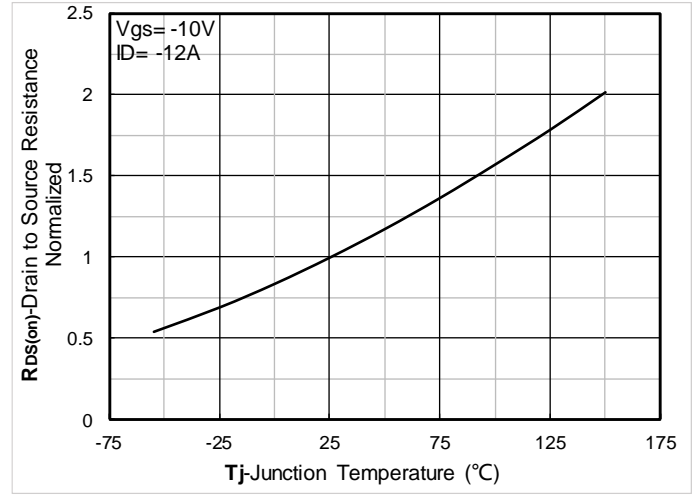


Figure 6. Normalized On-Resistance

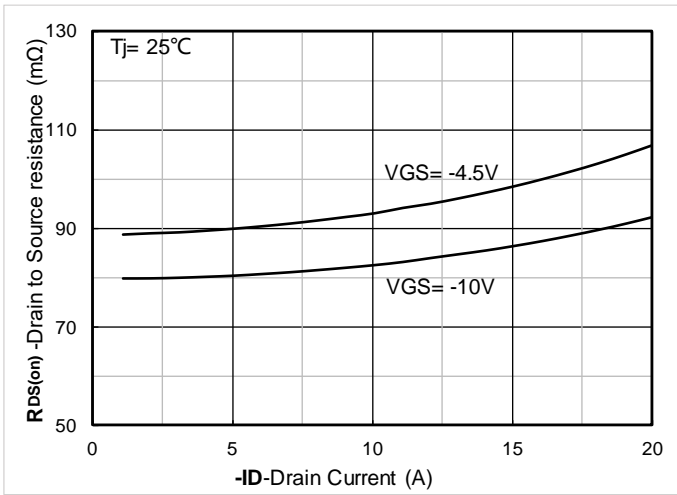


Figure 7. RDS(on) VS Drain Current

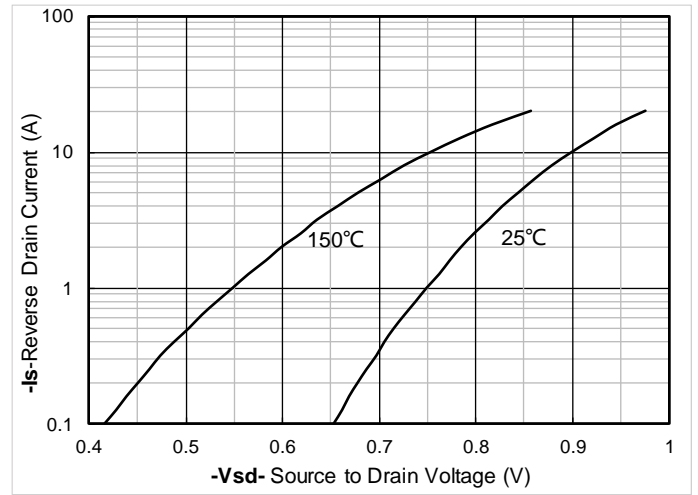


Figure 8. Forward characteristics of reverse diode

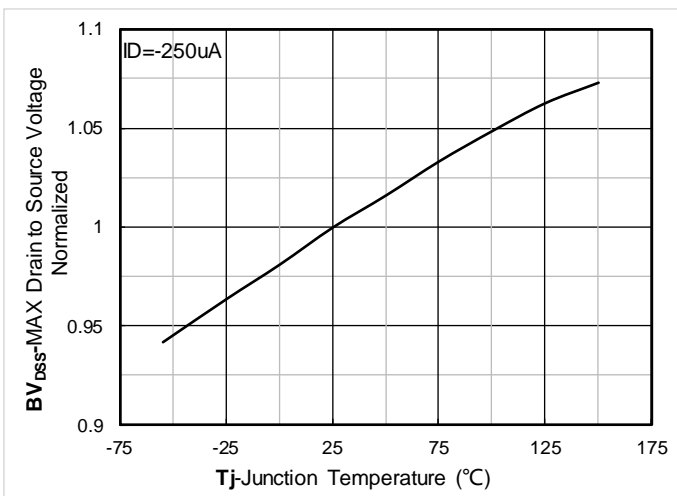


Figure 9. Normalized breakdown voltage

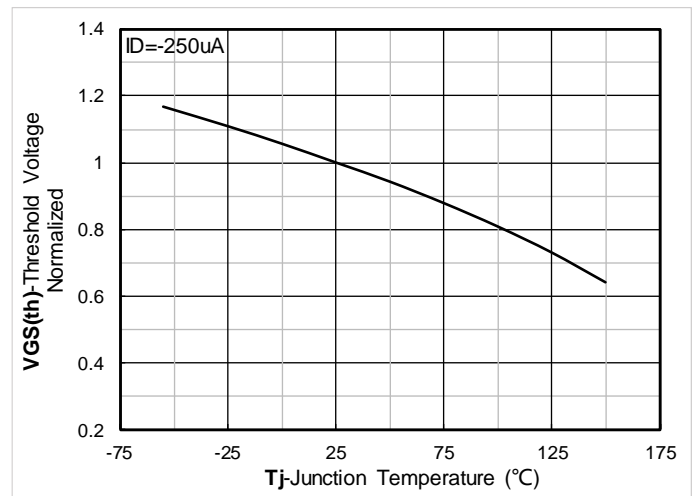


Figure 10. Normalized Threshold voltage



# YJG12NP10B

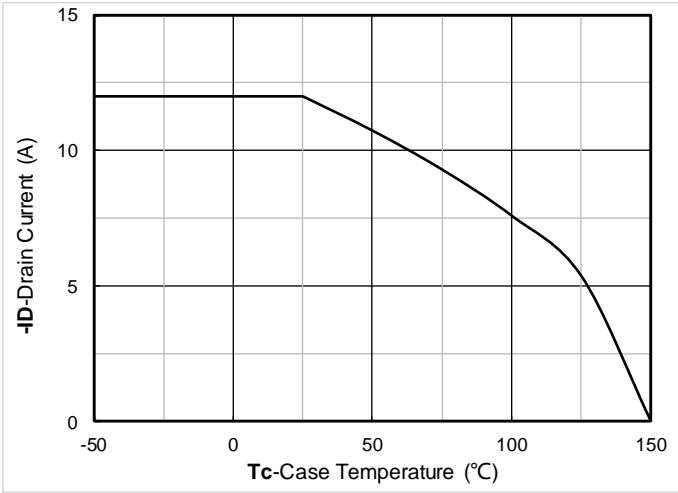


Figure 11. Current dissipation

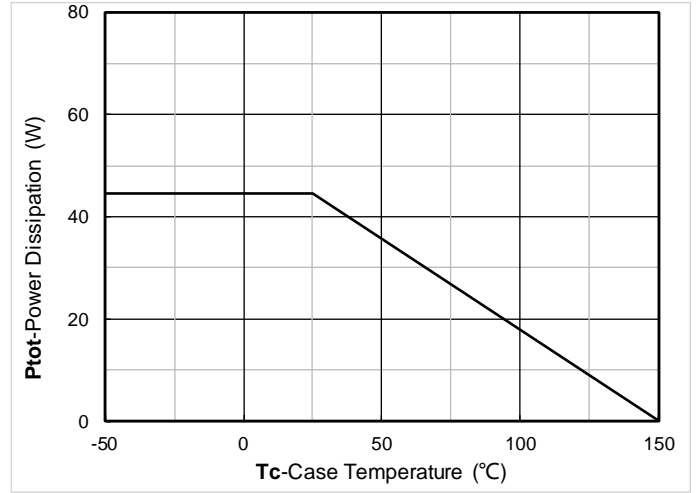


Figure 12. Power dissipation

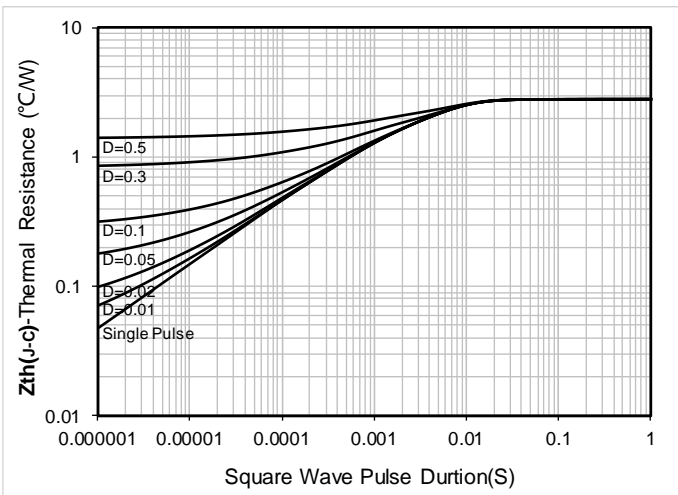


Figure 13. Maximum Transient Thermal Impedance

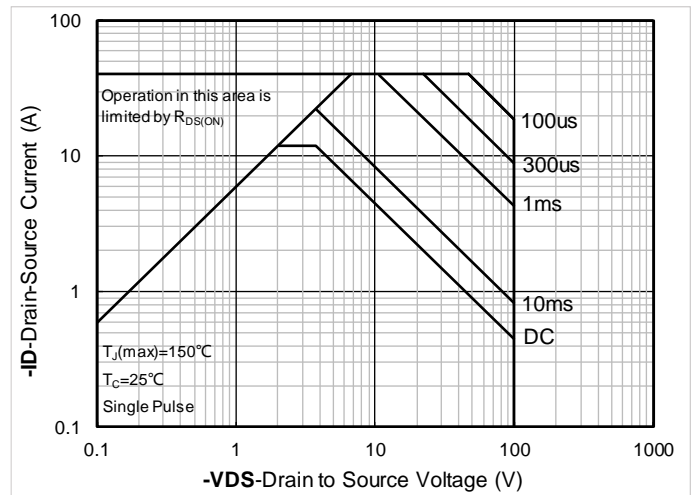


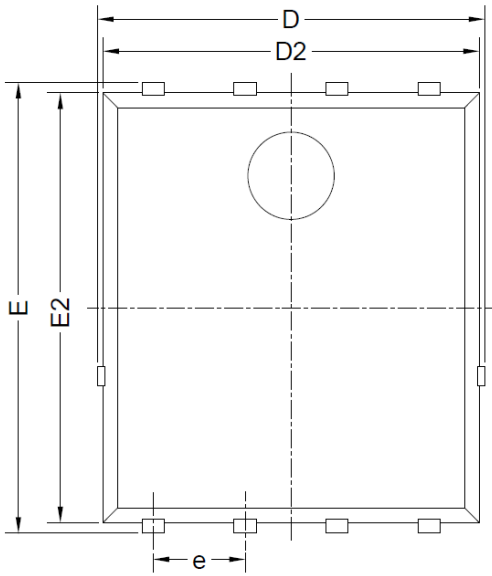
Figure 14. Safe Operation Area



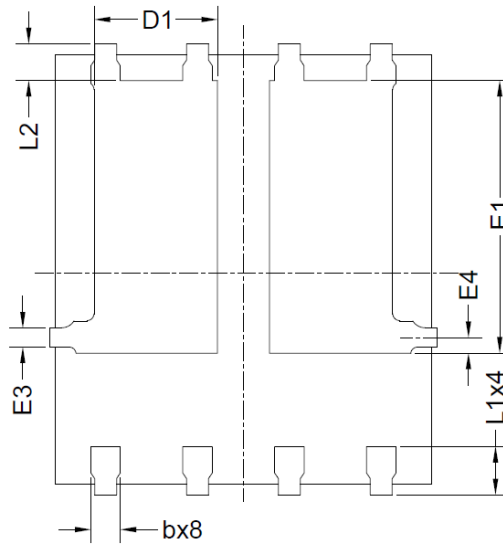


# YJG12NP10B

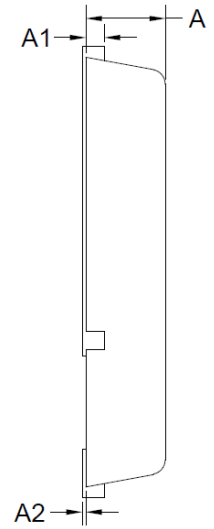
## ■ PDFN5060-8L-E-1.1MM Package information



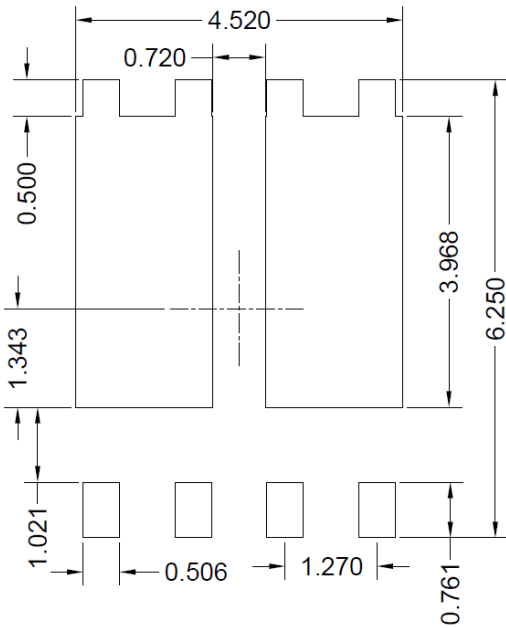
Top View  
正面视图



Bottom View  
背面视图



Side View  
侧面视图



Suggested Solder Pad Layout  
Top View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	1.50	1.70	1.90
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
E3	0.254REF		
E4	0.21REF		
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		

Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.10$ mm.
3. The pad layout is for reference purposes only.



## YJG12NP10B

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### Disclaimer

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